IN THE SPECIFICATION:

Paragraph beginning at line 7 of page 1 has been amended as follows:

Increases in the level of integration in LSI's and systemization have led to the possibility in recent years of small, highly functional electronic equipment such as personal computers and mobile telephones. Circuit patterns are drawn with a few million elements packed onto a semiconductor chip of a few millimeters ~~n~~ in every direction so as to have a line width from a micron order to a nano-order and development of lithographic technology for implementing this is expanding. Until ~~Up until~~ now, the main focus of lithography has been optical lithography technology. ~~Here,~~ There, the wavelength of light used is taken to be extremely short to correspond to the fine detail of the pattern, and short wavelength lasers were used. This processing has also, however, encountered problems with the optical systems and the resists and compatibility of the optical exposure devices with fine detail is also reaching its limit. Much is therefore expected from technology for replacing light with a source such as an electron beam or ultra-short-wave ultra-violet light.

Paragraph beginning at line 8 of page 6 has been amended as follows:

In accordance the present invention, there is provided a fine stencil structure correction device characterized by a device for irradiating and scanning with a charged particle beam so as to correct shapes of defects at locations of a fine stencil structure sample using an etching and/or deposition function, where means for detecting a transmitted beam is located ~~to~~ on the ~~rear~~ opposite side of the sample as viewed from the beam source. An absorbed current detector or a combination of a transmitted beam target and a secondary charged particle detector can be adopted as the detection means.

Paragraph beginning at line 12 of page 10 has been amended as follows:

The basic configuration of the present invention is shown in FIG. 1A. The apparatus has ~~structure of~~ a sample stage 30 for fixing and moving a sample relative to the FIB lens barrel 1, ~~and~~ the sample being a mask 3 for defect correction ~~(structure)~~, a secondary charged particle detector 4 for detecting secondary charged particles discharged from the sample 3 receiving the focused ion beam 2 and ~~the structure of~~ a gas gun (not shown). The foregoing elements

are ~~is~~ the same as those ~~that~~ of a conventional FIB device. The configuration specific to the present invention deploys a target for secondary electron generation 6 arranged at ~~to~~ the rear of the sample stage 30 and a secondary charged particle detector 5 arranged at the rear of the sample stage 30 for detecting secondary charged particles emitted from the ~~this~~ target 6. Further, the sample stage 30 is provided with a hole at a central portion to allow a primary beam (ions, electrons) to be incident from a vertical direction and detect transmitted particles of the primary beam in a vertical direction, and for carrying out detection of secondary particles. Further, the sample stage 30 has a function capable of controlling an angle of inclination of the mask with respect to an arbitrary direction in order to implement perpendicularity of the processing shape.

Paragraph beginning at line 16 of page 13 has been amended as follows:

It is necessary for the target for generating secondary electrons 12 to be positioned opposite the EB lens barrel 11 (FIB lens barrel 1) via the mask 3 on the trajectory of the electron beam. This position overlaps with the position of the ion beam trajectory between the FIB lens barrel 1 and the mask 3, and is therefore equipped with a

mechanism capable bringing the position of the detector in and out depending on ~~where~~ <u>whether</u> the detector is being used or not used. On the other hand, a secondary electron detector 5 for monitoring an SEM image on the rear surface of the mask and a target for generating secondary electrons 6 (transmission-type detector) for detecting an ion beam passing through the mask are provided at the side of the EB lens barrel 11. This target for generating secondary electrons 6 acts on the electron beam trajectory. It is therefore necessary to provide a mechansim capable of depositing and withdrawing the position of the detector according to whether it is being used or not.